

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS

- Anti-Parallel Diode

 Switchmode Power Supply
 Inverters
- Free Wheeling Diode
 - -Motor Controllers
 - -Converters
 - -Inverters
- Snubber Diode

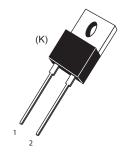
• PFC

PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular TO-220 Package
- Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Low Losses
- · Low Noise Switching
- Cooler Operation
- · Higher Reliability Systems
- Increased System Power Density





- 1 Cathode
- 2 Anode
 - Back of Case Cathode

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT15D120K(G)	UNIT
V _R	Maximum D.C. Reverse Voltage		
V _{RRM}	Maximum Peak Repetitive Reverse Voltage	1200	Volts
V _{RWM}	Maximum Working Peak Reverse Voltage		
I _{F(AV)}	Maximum Average Forward Current (T _C = 123°C, Duty Cycle = 0.5)	15	
I _{F(RMS)}	RMS Forward Current (Square wave, 50% duty)	27	Amps
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 45°C, 8.3ms)	110	
T _J ,T _{STG}	Operating and StorageTemperature Range	-55 to 175	°C
T _L	Lead Temperature for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

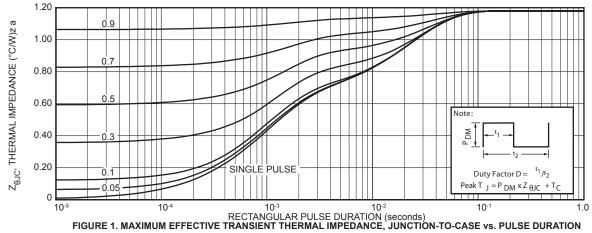
Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V _F	Forward Voltage	I _F = 15A		2.0	2.5	Volts
		I _F = 30A		2.3		
		I _F = 15A, T _J = 125°C		1.8		
I _{RM}	Maximum Reverse Leakage Current	V _R = V _R Rated			250	- μΑ
		$V_R = V_R$ Rated, $T_J = 125$ °C			500	
C _T	Junction Capacitance, V _R = 200V			17		pF

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t _{rr}	Reverse Recovery Time $I_F = 1A$, $di_F/dt = -100A/\mu s$, $V_R = 30V$, $T_J = 25$ °C		-	32		ns
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -200A/\mu s$ $V_R = 800V$, $T_C = 25^{\circ}C$	-	260		115
Q _{rr}	Reverse Recovery Charge		-	480		nC
I _{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -200A/\mu s$ $V_R = 800V$, $T_C = 125^{\circ}C$	-	370		ns
Q _{rr}	Reverse Recovery Charge		-	1300		nC
I _{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t _{rr}	Reverse Recovery Time	$I_F = 15A$, $di_F/dt = -1000A/\mu s$ $V_R = 800V$, $T_C = 125°C$	-	140		ns
Q _{rr}	Reverse Recovery Charge		-	2000		nC
I _{RRM}	Maximum Reverse Recovery Current		-	28		Amps

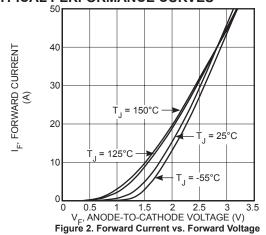
THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.18	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			80	
W _T	Package Weight		0.07		OZ
			1.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.



TYPICAL PERFORMANCE CURVES



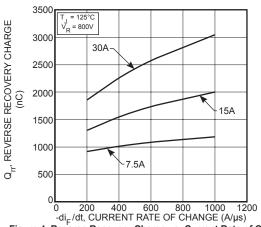
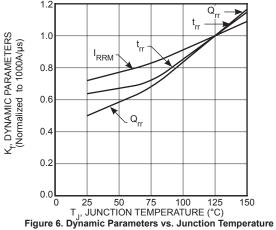
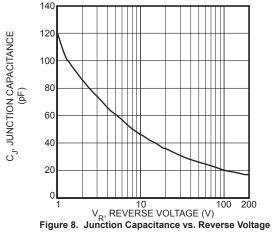


Figure 4. Reverse Recovery Charge vs. Current Rate of Change





APT15D120K(G)

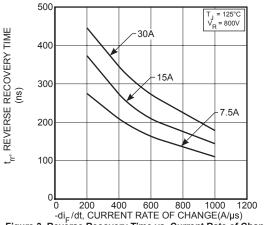


Figure 3. Reverse Recovery Time vs. Current Rate of Change

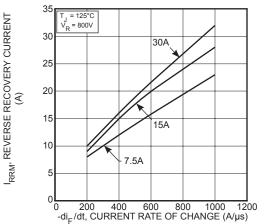


Figure 5. Reverse Recovery Current vs. Current Rate of Change

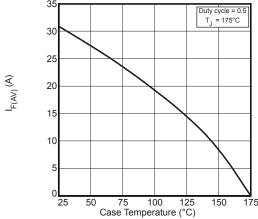


Figure 7. Maximum Average Forward Current vs. CaseTemperature

Figure 9. Diode Test Circuit

- I_F Forward Conduction Current
- di_r/dt Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} Maximum Reverse Recovery Current
- 4 t_{rr} Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25, I_{RRM} passes through zero.
- $\mathbf{5}$ \mathbf{Q}_{rr} Area Under the Curve Defined by \mathbf{I}_{RRM} and \mathbf{t}_{RRM}

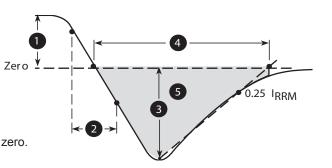
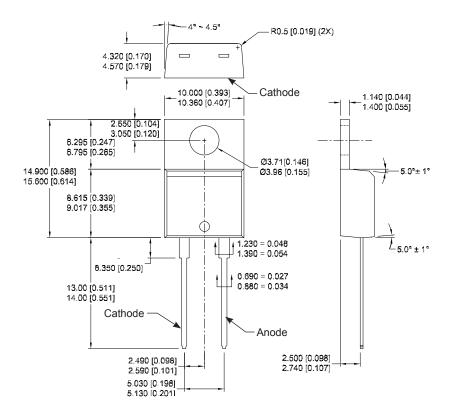


Figure 10. Diode Reverse Recovery Waveform Definition

TO-220 (K) Package Outline e3 100% Sn



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